

CMPT3904 CMPT3904G* NPN
 CMPT3906 CMPT3906G* PNP

**SURFACE MOUNT SILICON
 COMPLEMENTARY TRANSISTORS**



SOT-23 CASE

* Device is *Halogen Free* by design



www.centrasemi.com

DESCRIPTION:

These CENTRAL SEMICONDUCTOR devices are complementary silicon transistors manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for small signal general purpose amplifier and switching applications.

**MARKING CODES: CMPT3904: C1A
 CMPT3906: C2A
 CMPT3904G*: CG1
 CMPT3906G*: CG2**

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Collector-Base Voltage
 Collector-Emitter Voltage
 Emitter-Base Voltage
 Continuous Collector Current
 Power Dissipation
 Operating and Storage Junction Temperature
 Thermal Resistance

SYMBOL	CMPT3904	CMPT3906	UNITS
	CMPT3904G*	CMPT3906G*	
V_{CBO}	60	40	V
V_{CEO}	40	40	V
V_{EBO}	6.0	5.0	V
I_C		200	mA
P_D		350	mW
T_J, T_{stg}	-65 to +150		$^\circ\text{C}$
θ_{JA}	357		$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$)

SYMBOL	TEST CONDITIONS
I_{CEV}	$V_{CE}=30\text{V}, V_{EB}=3.0\text{V}$
I_{BL}	$V_{CE}=30\text{V}, V_{EB}=3.0\text{V}$
BV_{CBO}	$I_C=10\mu\text{A}$
BV_{CEO}	$I_C=1.0\text{mA}$
BV_{EBO}	$I_E=10\mu\text{A}$
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$
$V_{CE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$
$V_{BE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$
h_{FE}	$V_{CE}=1.0\text{V}, I_C=0.1\text{mA}$
h_{FE}	$V_{CE}=1.0\text{V}, I_C=1.0\text{mA}$
h_{FE}	$V_{CE}=1.0\text{V}, I_C=10\text{mA}$
h_{FE}	$V_{CE}=1.0\text{V}, I_C=50\text{mA}$
h_{FE}	$V_{CE}=1.0\text{V}, I_C=100\text{mA}$

SYMBOL	CMPT3904 CMPT3904G*		CMPT3906 CMPT3906G*		UNITS
	MIN	MAX	MIN	MAX	
I_{CEV}	-	50	-	50	nA
I_{BL}	-	50	-	50	nA
BV_{CBO}	60	-	40	-	V
BV_{CEO}	40	-	40	-	V
BV_{EBO}	6.0	-	5.0	-	V
$V_{CE(SAT)}$	-	0.20	-	0.25	V
$V_{CE(SAT)}$	-	0.30	-	0.40	V
$V_{BE(SAT)}$	0.65	0.85	0.65	0.85	V
$V_{BE(SAT)}$	-	0.95	-	0.95	V
h_{FE}	40	-	60	-	
h_{FE}	70	-	80	-	
h_{FE}	100	350	100	300	
h_{FE}	60	-	60	-	
h_{FE}	30	-	30	-	

CMPT3904 CMPT3904G* NPN
 CMPT3906 CMPT3906G* PNP

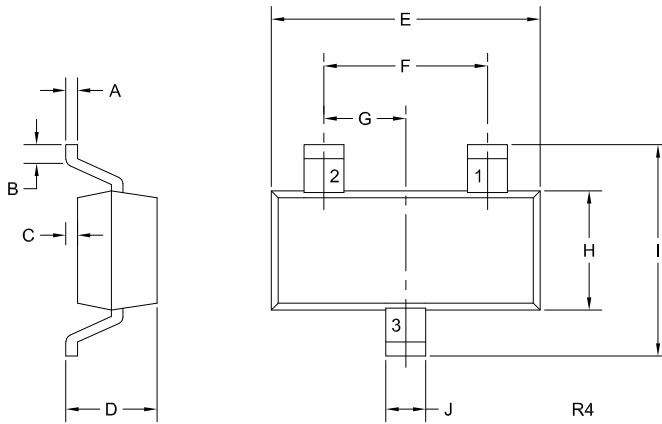
**SURFACE MOUNT SILICON
 COMPLEMENTARY TRANSISTORS**



ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^\circ\text{C}$)

SYMBOL	TEST CONDITIONS	CMPT3904 CMPT3904G*		CMPT3906 CMPT3906G*		UNITS
		MIN	MAX	MIN	MAX	
f_T	$V_{CE}=20\text{V}$, $I_C=10\text{mA}$, $f=100\text{MHz}$	300	-	250	-	MHz
C_{ob}	$V_{CB}=5.0\text{V}$, $I_E=0$, $f=1.0\text{MHz}$	-	4.0	-	4.5	pF
C_{ib}	$V_{BE}=0.5\text{V}$, $I_C=0$, $f=1.0\text{MHz}$	-	12	-	12	pF
t_d	$V_{CC}=3.0\text{V}$, $V_{BE}=0.5$, $I_C=10\text{mA}$, $I_{B1}=1.0\text{mA}$	-	35	-	35	ns
t_r	$V_{CC}=3.0\text{V}$, $V_{BE}=0.5$, $I_C=10\text{mA}$, $I_{B1}=1.0\text{mA}$	-	35	-	35	ns
t_s	$V_{CC}=3.0\text{V}$, $I_C=10\text{mA}$, $I_{B1}=I_{B2}=1.0\text{mA}$	-	200	-	225	ns
t_f	$V_{CC}=3.0\text{V}$, $I_C=10\text{mA}$, $I_{B1}=I_{B2}=1.0\text{mA}$	-	50	-	75	ns

SOT-23 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.044	0.89	1.12
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.104	2.10	2.64
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R4)

LEAD CODE:

- 1) Base
- 2) Emitter
- 3) Collector

MARKING CODES:

CMPT3904: C1A
 CMPT3906: C2A
 CMPT3904G*: CG1
 CMPT3906G*: CG2

* Device is *Halogen Free* by design

R11 (11-June 2021)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix " TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix " PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

Corporate Headquarters & Customer Support Team

Central Semiconductor Corp.
145 Adams Avenue
Hauppauge, NY 11788 USA
Main Tel: (631) 435-1110
Main Fax: (631) 435-1824
Support Team Fax: (631) 435-3388
www.centrasemi.com

Worldwide Field Representatives:
www.centrasemi.com/wwreps

Worldwide Distributors:
www.centrasemi.com/wwdistributors

For the latest version of Central Semiconductor's **LIMITATIONS AND DAMAGES DISCLAIMER**, which is part of Central's Standard Terms and Conditions of sale, visit: www.centrasemi.com/terms